

Amendments to the Claims:

Please cancel claims 1 - 6 and 12 - 18, which stand withdrawn from consideration as being directed to a non-elected invention, without prejudice or disclaimer of the subject matter thereof and without prejudice to the right to file a divisional application directed thereto.

Please amend claims 7, 8 and 19 as follows.

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 6 (canceled)

7. (currently amended)      A process of fabricating a display device for obtaining an active matrix substrate for use in a display device by placing an insulating substrate with an amorphous semiconductor film or a granular polycrystalline semiconductor film formed on the top surface thereof on a stage, irradiating laser light to a plurality of regions on the amorphous semiconductor film or the granular polycrystalline semiconductor film on the insulating substrate so as to be annealed, reforming the amorphous semiconductor film or the granular polycrystalline semiconductor film into polycrystalline semiconductor film containing band-like shape crystal grains,

said process comprising the steps of:

using continuous-wave laser light condensed into linear or rectangular form as the laser light;

continuously shifting the insulating substrate in a shifting direction transverse to the longitudinal direction of the linear form or the rectangular form of the laser light;

detecting a location of the insulating substrate relative to an irradiation position of the laser light for every shift of the insulating substrate of a predetermined distance in the shifting direction; and

repeating an operation of starting irradiation of the continuous-wave laser light at a time when respective regions of the insulating substrate to be irradiated with the laser light reach the irradiation position of the laser light, and then stopping irradiation of the continuous-wave laser light at a time when the respective regions of the insulating substrate to be irradiated with the laser light pass the irradiation position of the laser light;

wherein a repeating operation of starting and stopping irradiation of the continuous-wave laser light is effected in accordance with the detection of the location of the insulating substrate; and

thereby discontinuously forming the band-like shape crystal grains of the polycrystalline semiconductor film as reformed in relation to the shifting direction of the insulating substrate.

8. (currently amended) A process of fabricating a display device according to claim 7, further comprising the step of

starting irradiation of the continuous-wave laser light upon start of ~~movement~~ shifting of the insulating substrate at irradiation energy density equivalent to not more than one third of a value suitable for reformation of the amorphous semiconductor film or the granular polycrystalline semiconductor film,

setting the irradiation energy density of the continuous-wave laser light at the value suitable for reformation of the amorphous semiconductor film or the granular polycrystalline semiconductor film at a time when respective regions where the reformation is to be made in a state of continuously ~~moving~~ shifting the insulating substrate, and

reducing the irradiation energy density of the continuous-wave laser light to not more than one third of a value suitable for reformation of the amorphous semiconductor film or the granular polycrystalline semiconductor film at a time when respective regions where the reformation is to be made is passed.

9. (original) A process of fabricating a display device according to claim 7, where the respective regions where the reformation is to be made are active regions of thin-film transistors, and the periphery thereof.

10. (original) A process of fabricating a display device according to claim 9, where the insulating substrate is a glass substrate and the respective regions where the reformation is to be made are regions where active regions of driver thin-film transistors are formed.

11. (original) A process of fabricating a display device according to claim 7, where the continuous-wave laser light is the second harmonics of LD (laser diode) pumped YVO<sub>4</sub> continuous wave laser.

Claims 12 - 18 (canceled)

19. (currently amended) A process of fabricating a display device for obtaining an active matrix substrate for use in a, display device by placing an insulating substrate with an amorphous semiconductor film or a granular polycrystalline semiconductor film formed on the top surface thereof on a stage, irradiating laser light to a plurality of regions on the amorphous semiconductor film or the granular polycrystalline semiconductor film on the insulating substrate so as to be annealed, reforming the amorphous semiconductor film or the granular polycrystalline semiconductor film into polycrystalline semiconductor film containing band-like shape crystal grains, said process comprising the steps of:

using continuous-wave laser light condensed into linear or rectangular form as the laser light;

continuously moving the insulating substrate in a direction crossing the linear form or the longitudinal direction of the rectangular form; and

detecting a location of the insulating substrate relative to an irradiation position of the laser light for every movement of the insulating substrate of a predetermined distance in the moving direction; and

repeating operation of starting irradiation of the continuous-wave laser light at a time when respective regions of the insulating substrate to be irradiated with the laser light are reached and stopping irradiation of the continuous-wave laser light at a time when the respective regions of the insulating substrate to be irradiated with the laser light are passed, thereby forming the band-like shape crystal grains of the polycrystalline semiconductor film as reformed at given pitches to an equal size in relation to a moving direction of the insulating substrate.